Specifcation of products

：

：MURP400200N-K3

ZHEJIANG SHILING SEMICONDUCTOR CO.,LTD.

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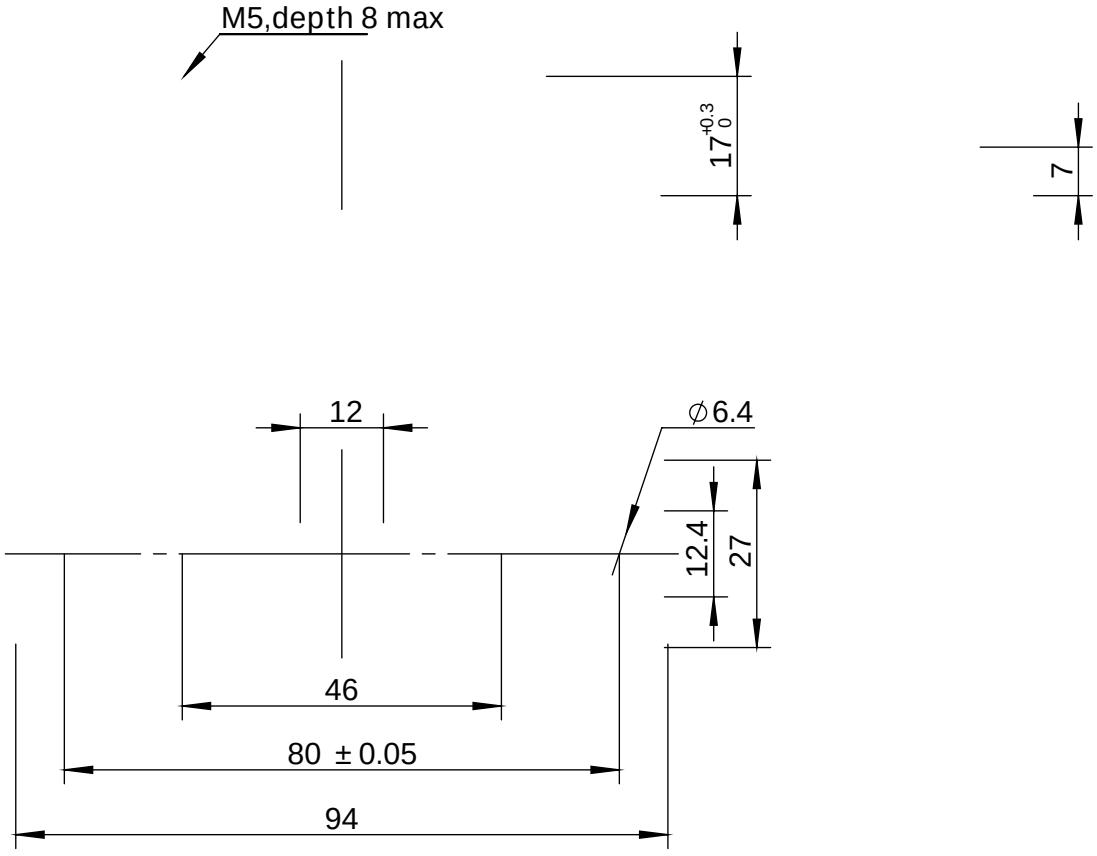
05 2023.8

ELECTRICAL CHARACTERISTICS

T_C=25 unless otherwise specified

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{RM}	Reverse Leakage Current	V_R=200V	--	--	1	mA
		V_R=200V, T_J=125	--	--	2	mA
V_F	Forward Voltage	I_F=200A	--	0.95	1.30	V
		I_F=200A, T_J=125	--	--	1.20	V
t_{rr}	Reverse Recovery Time	I_F=1A, V_R=30V, di_F/dt=-200A/μs	--	43	--	ns
t_{rr}	Reverse Recovery Time	V_R=100V, I_F=200A	--	90	--	ns
I_{RRM}	Max. Reverse Recovery Current	di_F/dt=-100A/μs, T_J=25	--	5	--	A
t_{rr}	Reverse Recovery Time	V_R=100V, I_F=200A	--	112	--	ns
I_{RRM}	Max. Reverse Recovery Current	di_F/dt=-100A/μs, T_J=125	--	6.8	--	A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7
12
∅6.4
12.4
27
46
80 ± 0.05
94